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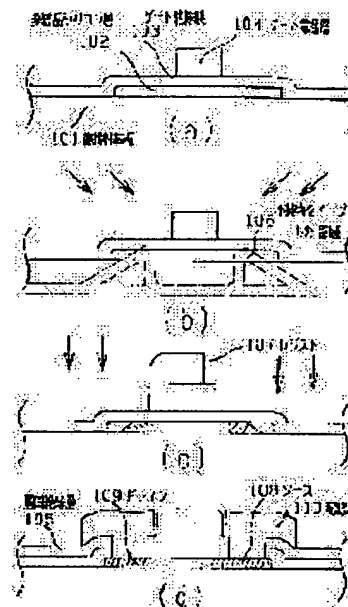
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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To form an offset region of a film transistor excellently in reproducibility by implanting the ions of impurities at a specified angle to the direction vertical to a substrate with energy penetrating a gate electrode.

CONSTITUTION: Ions of impurities are implanted at an angle of 30° or over to the direction vertical to a substrate with energy penetrating a gate electrode layer 104. In the place where they pass the gate electrode layer 104, the distribution becomes shallow, and they are distributed in a polycrystalline silicon layer 102. The place where the distribution of impurities becomes shallow can be controlled by changing the condition of ion implantation. Offset can be provided between the gate electrode and the place where distribution of impurities becomes shallow by selecting the proper condition of ion implantation. Hereby, the drive capacity of a film transistor can be improved.



LEGAL STATUS

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